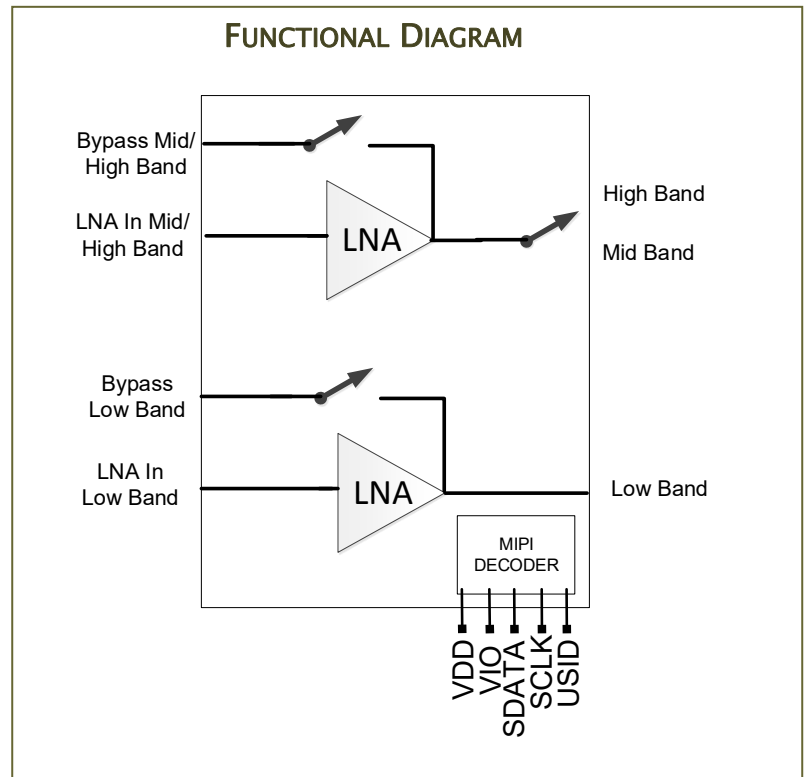


## Advanced Technical Data

### Features

- ☑ CMOS SOI Dual LNA for Low, Mid and High Band LTE receive applications.
- ☑ Integrated MIPI decoder with pin configurable default USID.
- ☑ ESD protection on all ports including ESD protection between MIPI controller and RF ports.
- ☑ Noise Figure < 1dB
- ☑ Gain > 15dB
- ☑ Single supply with 2.3V to 3.4V operating range.
- ☑ No external capacitors required if no DC applied on RF lines.
- ☑ Small die for flip-chip assembly.



### Description

The FE432701 is a CMOS SOI Dual LNA for LTE applications. It integrates a Low Band LNA and a Mid/High Band LNA.

Each LNA is individually selectable. In active mode the LNA's provide greater than 15dB gain and less than 1dB Noise Figure. Both LNA's incorporate a bypass path with loss of 2dB.

The device integrates a decoder compliant with the MIPI standard and the default USID is pin configurable allowing two instances of this device to be identified.

The LNA's run from a single supply with an operating range from 2.3V up to 3.4V. External DC blocking capacitors are not required on the RF ports unless there is a DC voltage

externally applied to the ports.

The device is fabricated using a high performance CMOS SOI process optimized for RF front-end applications. It delivers low noise across all the 4G bands, enabling high sensitivity and high linearity receive paths.

The FE432701 integrates ESD protection on all ports but also integrates ESD protection between the RF ports and the MIPI controller to support high reliability manufacturing.

The die will be available in die form for flip-chip assembly and will be RoHS compliant to EU Directive 2002/95/EC.

## Further Information

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